AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of the Claims:

1. (Currently Amended) A sputtering system comprising:

a semiconductor target material comprising a semiconductor material; and

a part coated with a spray material comprising the same material as the semiconductor target material.

2-30. (Canceled)

31. (New) A sputtering system according to claim 1, wherein the part is one of the group consisting of a target shield, a contamination plate, a backing plate, a current plate, a substrate holder, a gas introducing tube, and an inner wall of a chamber.

32. (New) A sputtering system according to claim 1, wherein the semiconductor material is silicon.

33. (New) A sputtering system comprising:

a semiconductor target comprising a semiconductor material; and

a part coated with a spray material comprising an oxide of the semiconductor material.

34. (New) A sputtering system according to claim 33, wherein the part is one of the group consisting of a target shield, a contamination plate, a backing plate, a current plate, a substrate holder, a gas introducing tube, and an inner wall of a chamber.

35. (New) A sputtering system according to claim 33, wherein the semiconductor material is silicon.

36. (New) A sputtering system comprising:

a semiconductor target comprising a semiconductor material; and

a part coated with a spray material comprising a nitride of the semiconductor material.

37. (New) A sputtering system according to claim 36, wherein the part is one of the group consisting of a target shield, a contamination plate, a backing plate, a current plate, a substrate holder, a gas introducing tube, and an inner wall of a chamber.

38. (New) A sputtering system according to claim 36, wherein the semiconductor material is silicon.

39. (New) A method for manufacturing a thin film comprising:

preparing a sputtering system comprising a semiconductor target comprising a semiconductor material, and a part coated with a spray material; and

forming a semiconductor film comprising the same material as the semiconductor target in the sputtering system,

wherein the spray material comprises one of the same material as the semiconductor target, an oxide of the semiconductor material and a nitride of the semiconductor material.

40. (New) A method according to claim 39, wherein the part is one of the group consisting of a target shield, a contamination plate, a backing plate, a current plate, a substrate holder, a gas introducing tube, and an inner wall of a chamber.

41. (New) A method according to claim 39, wherein the semiconductor material is silicon.

42. (New) A method according to claim 39, wherein the semiconductor target is connected to a high-frequency power source and the high-frequency power is applied to perform sputtering in an atmosphere including rare gas.

43. (New) A method for manufacturing a thin film comprising:

preparing a sputtering system comprising a semiconductor target comprising a semiconductor material, and a part coated with a spray material; and

forming an oxide film comprising an oxide of the semiconductor material in the sputtering system,

wherein the spray material comprises one of the same material as the semiconductor target, an oxide of the semiconductor material and a nitride of the semiconductor material.

44. (New) A method according to claim 43, wherein the part is one of the group consisting of a target shield, a contamination plate, a backing plate, a current plate, a substrate holder, a gas introducing tube, and an inner wall of a chamber.

45. (New) A method according to claim 43, wherein the semiconductor material is silicon.

46. (New) A method according to claim 43, wherein the semiconductor target is connected to a high-frequency power source and the high-frequency power is applied to perform sputtering in an atmosphere including rare gas.

47. (New) A method for manufacturing a thin film comprising:

preparing a sputtering system comprising a semiconductor target comprising a semiconductor material, and a part coated with a spray material; and

forming a nitride film comprising a nitride of the semiconductor material in the sputtering system,

wherein the spray material comprises one of the same material as the semiconductor target, an oxide of the semiconductor material and a nitride of the semiconductor material.

48. (New) A method according to claim 47, wherein the part is one of the group consisting of a target shield, a contamination plate, a backing plate, a current plate, a substrate holder, a gas introducing tube, and an inner wall of a chamber.

49. (New) A method according to claim 47, wherein the semiconductor material is silicon.

50. (New) A method according to claim 47, wherein the semiconductor target is connected to a high-frequency power source and the high-frequency power is applied to perform sputtering in an atmosphere including rare gas.

51. (New) A method for manufacturing a light emitting device comprising steps of:

forming a first insulating film comprising silicon nitride or silicon oxynitride on a substrate;

forming a semiconductor layer over the first insulating film;

forming a gate insulating film over the semiconductor layer;

forming a gate electrode over the gate insulating film;

forming a second insulating film comprising silicon oxynitride over the gate electrode;

forming a third insulating film over the second insulating film

forming an anode electrically connected to the semiconductor film over the third insulating film;

forming a light emitting layer over the anode; and

forming a cathode over the light emitting layer,

wherein at least one of the first insulating film and the second insulating film is formed in a sputtering system,

wherein the sputtering system comprises a semiconductor target comprising a semiconductor material, and a part coated with a spray material, and

wherein the spray material comprises one of the same material as the semiconductor target, an oxide of the semiconductor material and a nitride of the semiconductor material.

52. (New) A method according to claim 51, wherein the part is one of the group consisting of a target shield, a contamination plate, a backing plate, a current plate, a substrate holder, a gas introducing tube, and an inner wall of a chamber.

53. (New) A method according to claim 51, wherein the semiconductor material is silicon.

54. (New) A method according to claim 51, wherein the semiconductor target is connected to a high-frequency power source and the high-frequency power is applied to perform sputtering in an atmosphere including rare gas.